

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D T _C = +25°C
-40V	70mΩ @ V _{GS} = -10V	-15A
	104mΩ @ V _{GS} = -4.5V	-14A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

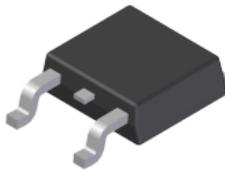
Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/contact-us) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

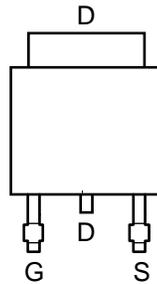
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (Approximate)

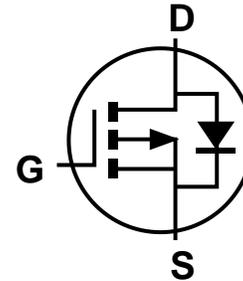
TO252 (DPAK)



Top View



Top View
Pin-Out



Equivalent Circuit

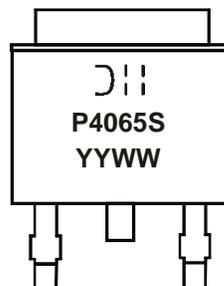
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP4065SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

TO252 (DPAK)



- ⏏ = Manufacturer's Marking
- P4065S = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Year (ex: 20 = 2020)
- WW = Week (01 to 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _C = +25°C	I _D	-15	A
		T _C = +70°C		-12	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-60	A
Maximum Body Diode Forward Current (Note 6)			I _S	-15	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-60	A
Avalanche Current, L = 0.1mH			I _{AS}	-14	A
Avalanche Energy, L = 0.1mH			E _{AS}	9.8	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	3.0	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R _{θJA}	42	°C/W
Total Power Dissipation (Note 6)			P _D	32	W
Thermal Resistance, Junction to Case (Note 6)		Steady State	R _{θJC}	3.9	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	µA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	53	70	mΩ	V _{GS} = -10V, I _D = -4.2A
			72	104		V _{GS} = -4.5V, I _D = -3.3A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	650	—	pF	V _{DS} = -20V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	55	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	43	—	pF	
Gate Resistance	R _g	—	14.4	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	6.1	—	nC	
Total Gate Charge (V _{GS} = -10V)	Q _g	—	12.2	—	nC	
Gate-Source Charge	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.4	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.6	—	ns	V _{DD} = -15V, V _{GS} = -10V, I _D = -1.0A, R _G = 6Ω
Turn-On Rise Time	t _R	—	2.9	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	36.3	—	ns	
Turn-Off Fall Time	t _F	—	15.3	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

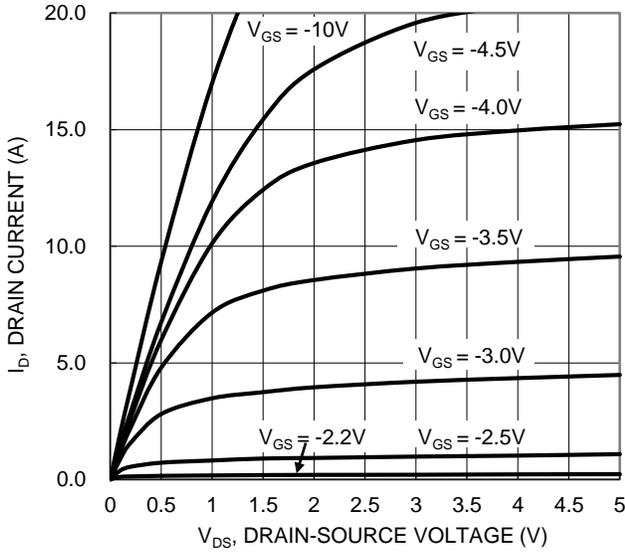


Figure 1. Typical Output Characteristic

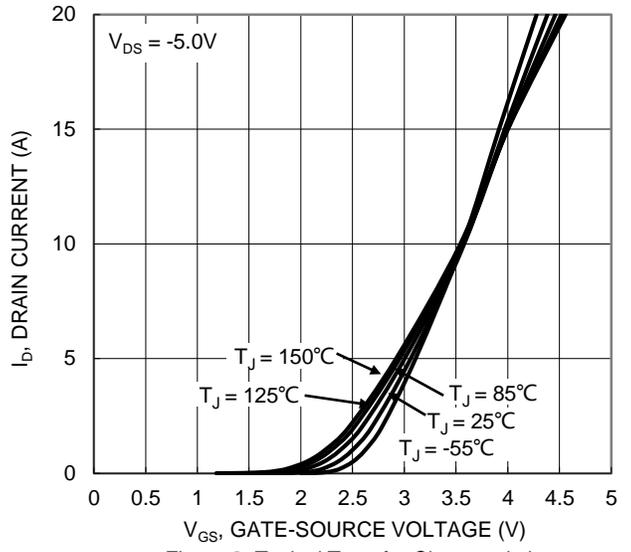


Figure 2. Typical Transfer Characteristic

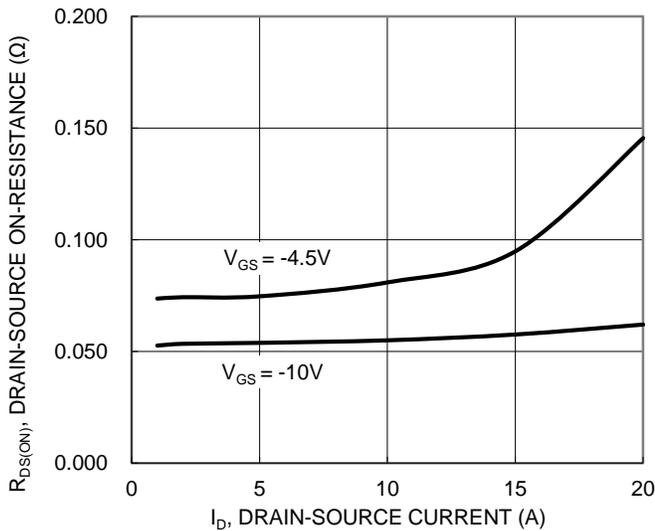


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

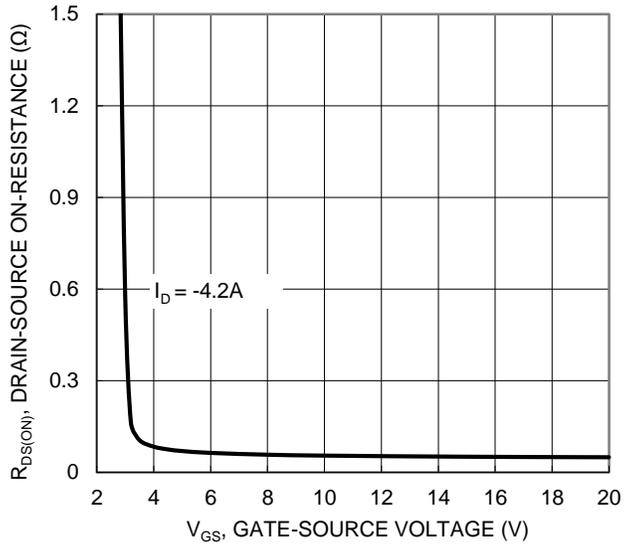


Figure 4. Typical Transfer Characteristic

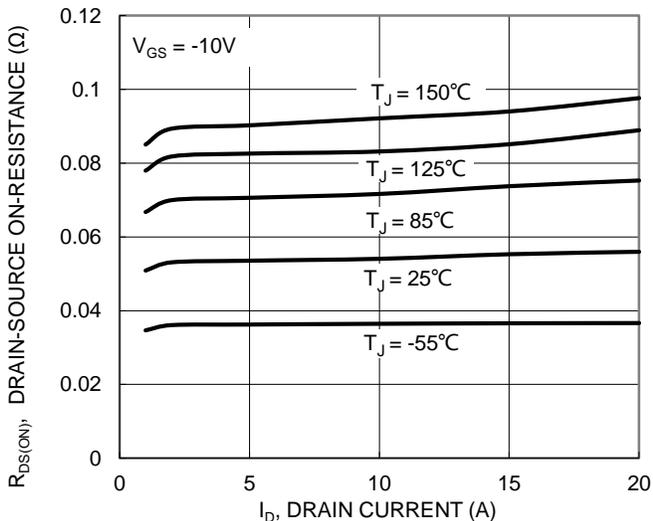


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

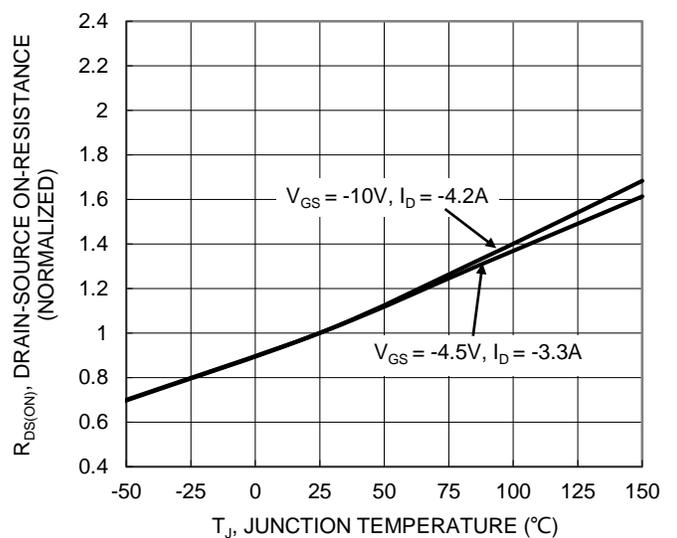
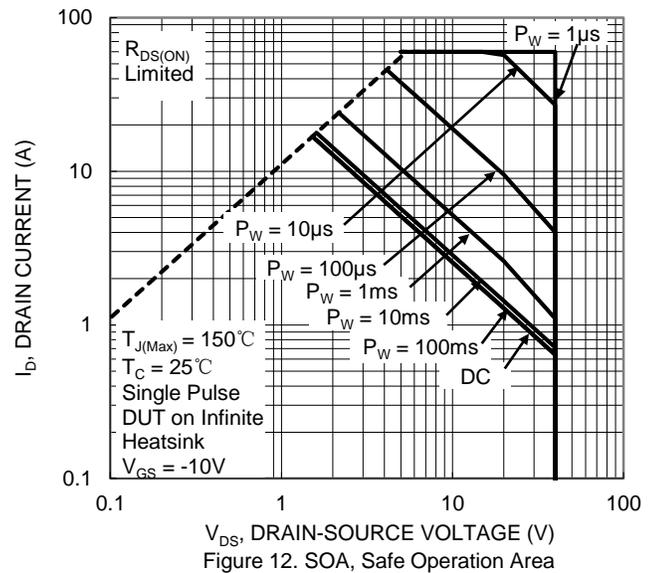
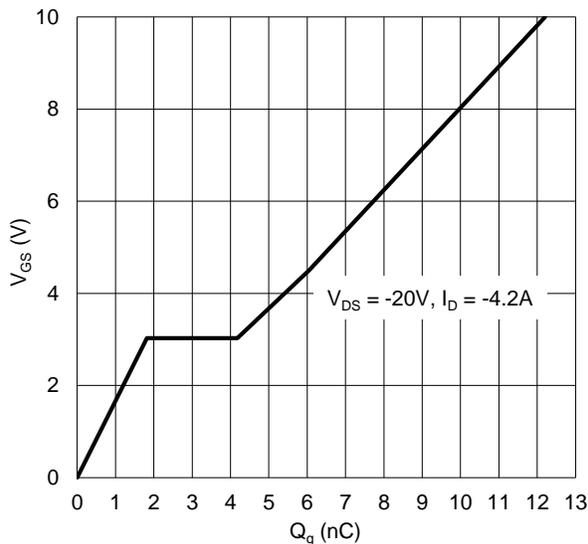
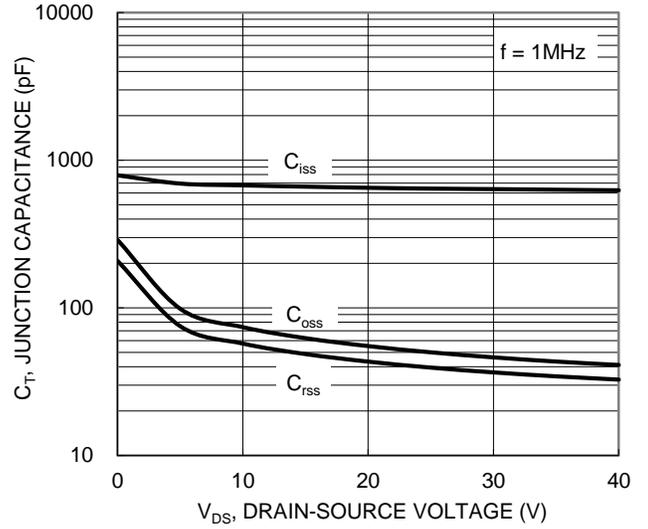
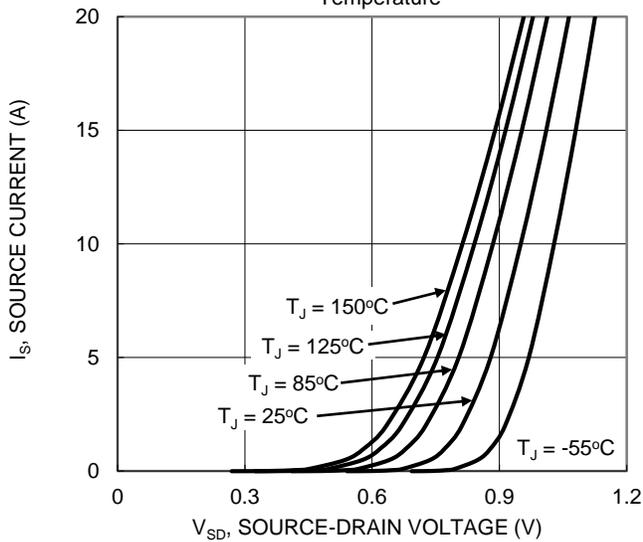
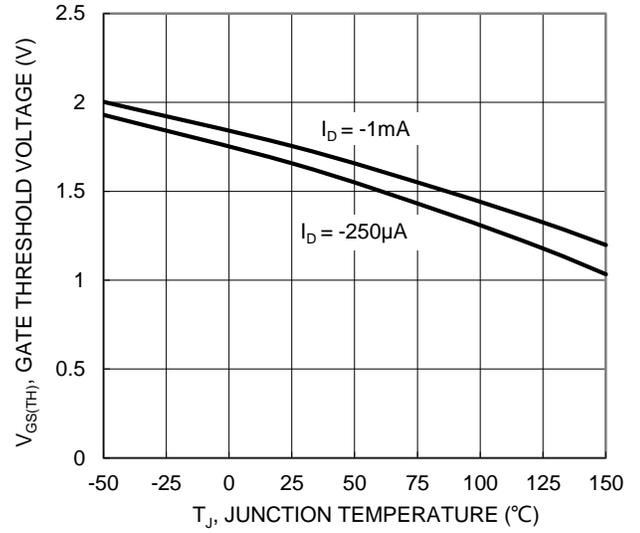
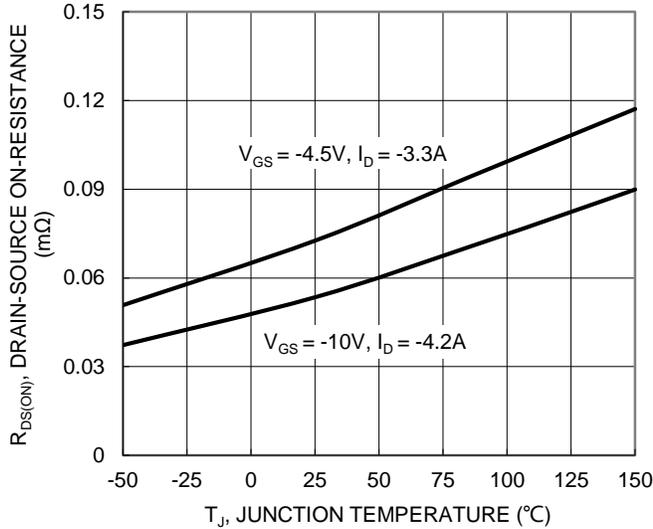


Figure 6. On-Resistance Variation with Junction Temperature



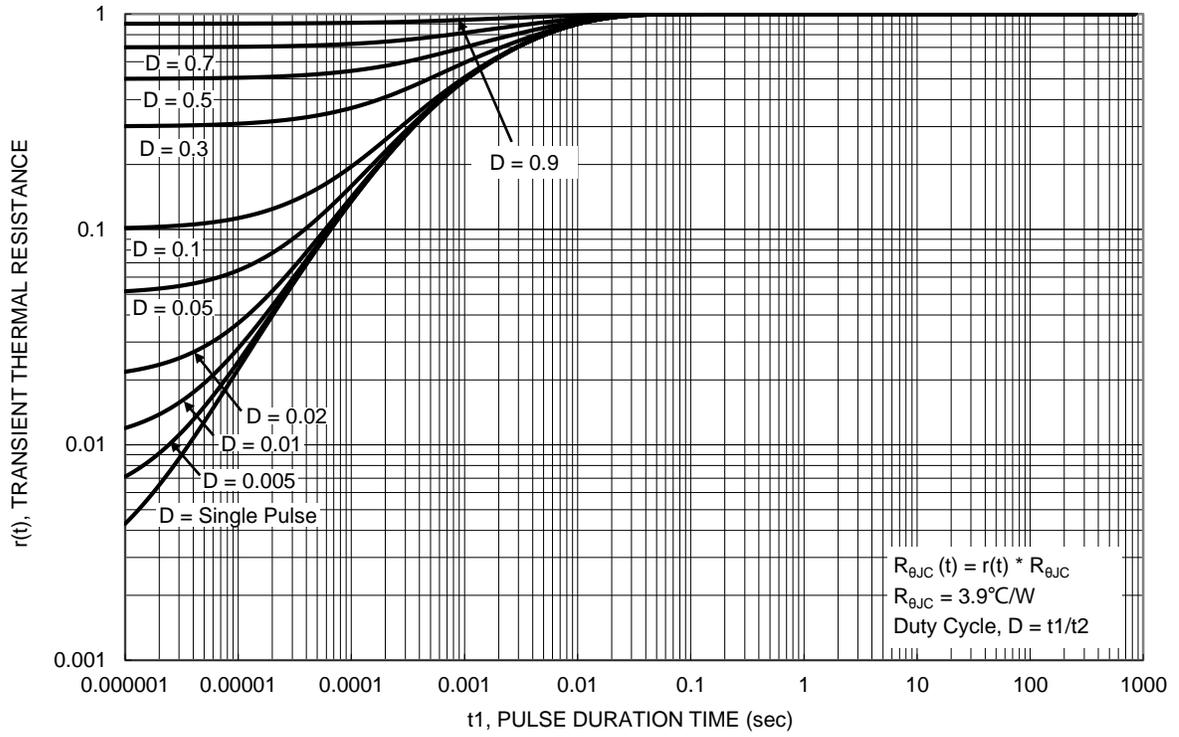
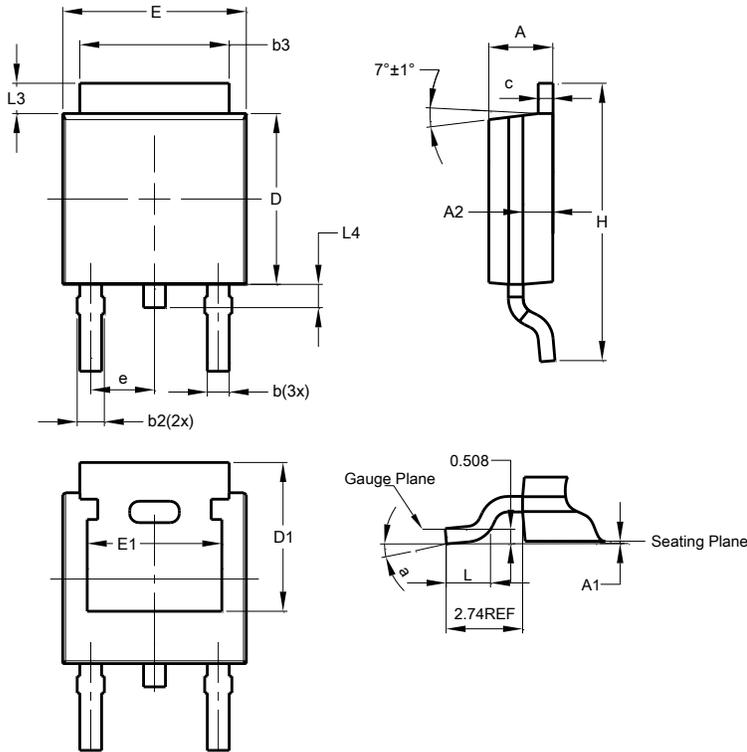


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

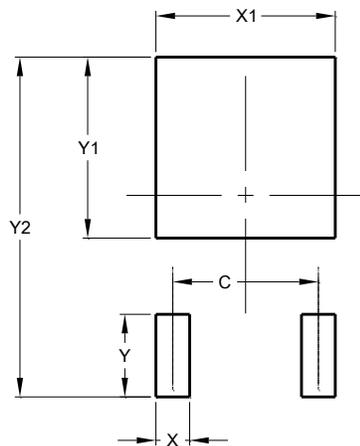


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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